

L Number	Hits	Search Text	DB	Time stamp
1	0	CMOS and transistor and CMP and oxide and tungsten and PEOX and gate and electrode and ILD and STI	USPAT	2004/10/26 15:17
4	0	CMOS and transistor and CMP and oxide and tungsten and gate and electrode and ILD and STI and (local adj interconnect) and (oxide adj chemical adj mechanical adj polish)	USPAT	2004/10/26 15:19
5	0	CMOS and (local adj interconnect) and (oxide adj chemical adj mechanical adj polish)	USPAT	2004/10/26 15:19
3	3	CMOS and transistor and CMP and oxide and tungsten and gate and electrode and ILD and STI and (local adj interconnect)	USPAT	2004/10/26 15:19
2	34	CMOS and transistor and CMP and oxide and tungsten and gate and electrode and ILD and STI	USPAT	2004/10/26 15:43
6	1	("5895239").PN.	USPAT	2004/10/26 15:43
7	1	((("5895239").PN.) and (CMOS or transistor or local or interconnect or opening or plug or CMP or doped or undoped or silicon or oxide o dioxide or thickness or gate oe electrode or gap or ILD or dielectric or stack or potion or trench or isolation polysilicon or PEOX or PETOS or CVD or HDP or PECVD)	USPAT	2004/10/26 15:57
8	1	("6130102").PN.	USPAT	2004/10/26 15:57
9	1	((("6130102").PN.) and (CMOS or transistor or local or interconnect or opening or plug or CMP or doped or undoped or silicon or oxide o dioxide or thickness or gate oe electrode or gap or ILD or dielectric or stack or potion or trench or isolation polysilicon or PEOX or PETOS or CVD or HDP or PECVD)	USPAT	2004/10/26 16:04
10	1	("5950102").PN.	USPAT	2004/10/26 16:04
11	1	((("6130102").PN.) and (CMOS or transistor or local or interconnect or opening or plug or CMP or doped or undoped or silicon or oxide o dioxide or thickness or gate oe electrode or gap or ILD or dielectric or stack or potion or trench or isolation polysilicon or PEOX or PETOS or CVD or HDP or PECVD)) and (CMOS or transistor or local or interconnect or opening or plug or CMP or doped or undoped or silicon or oxide o dioxide or thickness or gate oe electrode or gap or ILD or dielectric or stack or potion or trench or isolation polysilicon or PEOX or PETOS or CVD or HDP or PECVD)	USPAT	2004/10/26 16:06
12	1454	438/197	USPAT	2004/10/26 16:07
13	87	438/198	USPAT	2004/10/26 16:07
14	1320	438/199	USPAT	2004/10/26 16:07
15	171	438/954	USPAT	2004/10/26 16:08
16	1129	438/680	USPAT	2004/10/26 16:08
17	557	438/681	USPAT	2004/10/26 16:08
18	1035	438/683	USPAT	2004/10/26 16:08
19	1686	438/687	USPAT	2004/10/26 16:08
20	940	438/688	USPAT	2004/10/26 16:08
21	1413	438/700	USPAT	2004/10/26 16:08
22	847	438/712	USPAT	2004/10/26 16:08
23	1437	438/745	USPAT	2004/10/26 16:08
24	3248	438/692	USPAT	2004/10/26 16:08

10/26/04